



**AO4466**

**N-Channel Enhancement Mode Field Effect Transistor**

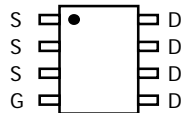


**General Description**

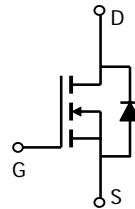
The AO4466 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance. *Standard Product AO4466 is Pb-free (meets ROHS & Sony 259 specifications). AO4466L is a Green Product ordering option. AO4466 and AO4466L are electrically identical.*

**Features**

$V_{DS}$  (V) = 30V  
 $I_D$  = 9.4A ( $V_{GS}$  = 10V)  
 $R_{DS(ON)}$  < 23m $\Omega$  ( $V_{GS}$  = 10V)  
 $R_{DS(ON)}$  < 35m $\Omega$  ( $V_{GS}$  = 4.5V)



**SOIC-8**



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	9.4	A
	$T_A=70^\circ\text{C}$	7.7	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	50	
Power Dissipation	$T_A=25^\circ\text{C}$	3.1	W
	$T_A=70^\circ\text{C}$	2.1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10\text{s}$	34	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	62	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	18	24	$^\circ\text{C/W}$	

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C		0.004	1	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.6	3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	20			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =9.4A T <sub>J</sub> =125°C		17	23	mΩ
				24	30	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		27	35	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =9.4A	10	24		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.75	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				4.3	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		621	820	pF
C <sub>oss</sub>	Output Capacitance			118		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			85		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		0.8	1.5	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =9.4A		11.3	17	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			5.7	8	nC
Q <sub>gs</sub>	Gate Source Charge			2.1		nC
Q <sub>gd</sub>	Gate Drain Charge			3		nC
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.6Ω, R <sub>GEN</sub> =3Ω		4.5	6.5	ns
t <sub>r</sub>	Turn-On Rise Time			3.1	5	ns
t <sub>D(off)</sub>	Turn-Off Delay Time			15.1	23	ns
t <sub>f</sub>	Turn-Off Fall Time			2.7	5	ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =9.4A, di/dt=100A/μs		15.5	21	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =9.4A, di/dt=100A/μs		7.1	10	nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t<sub>θ</sub> ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

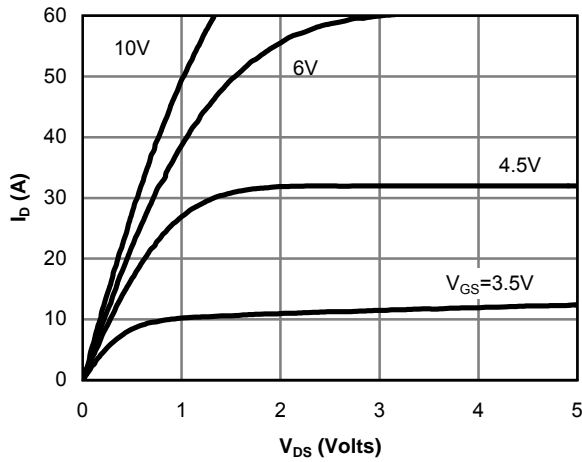


Fig 1: On-Region Characteristics

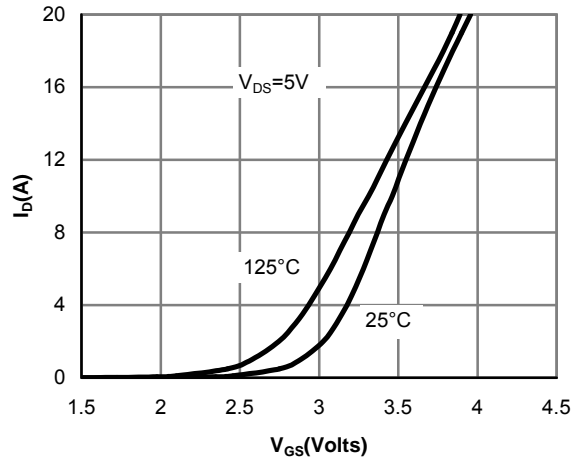


Figure 2: Transfer Characteristics

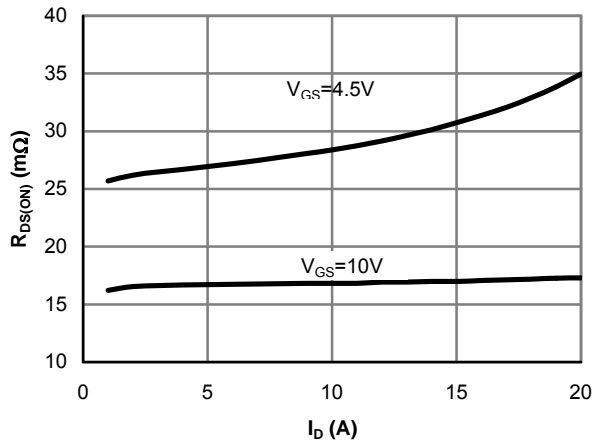


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

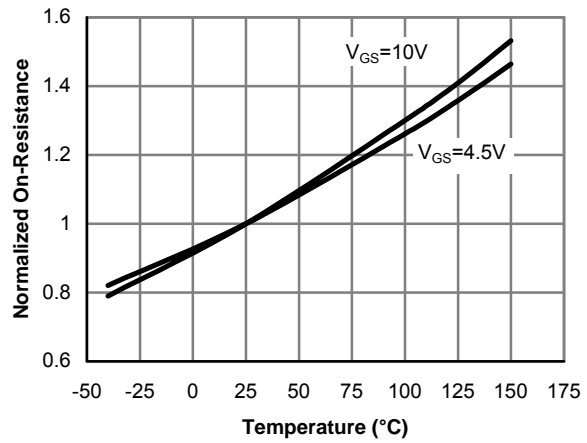


Figure 4: On-Resistance vs. Junction Temperature

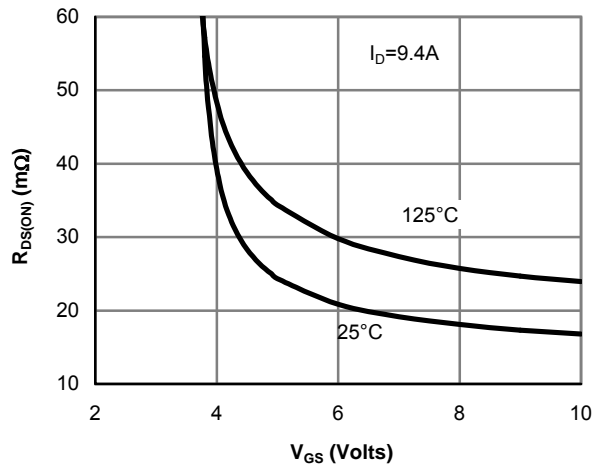


Figure 5: On-Resistance vs. Gate-Source Voltage

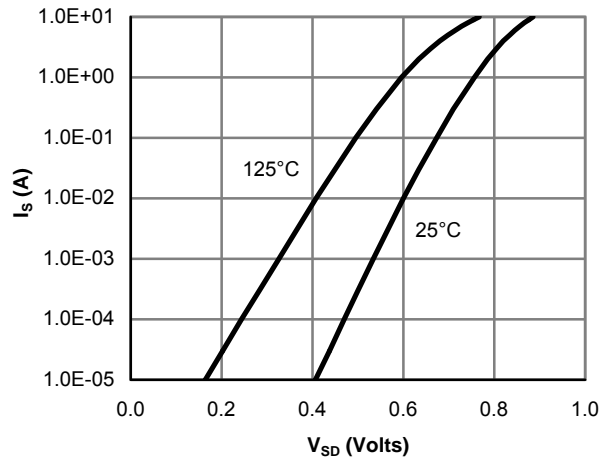


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

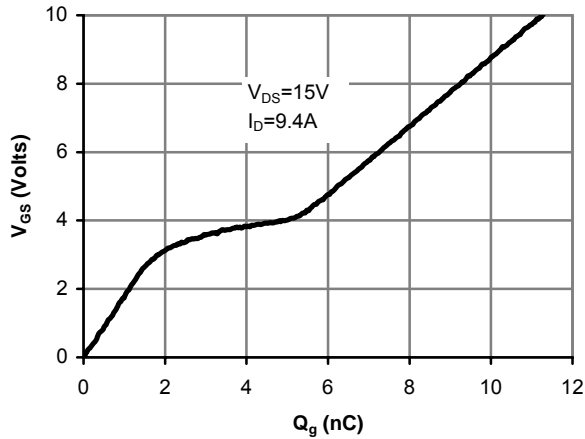


Figure 7: Gate-Charge Characteristics

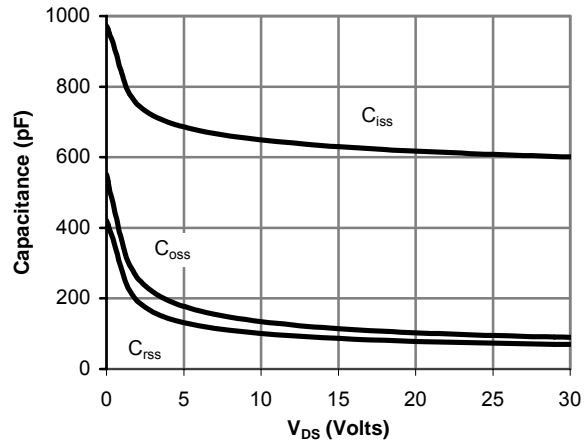


Figure 8: Capacitance Characteristics

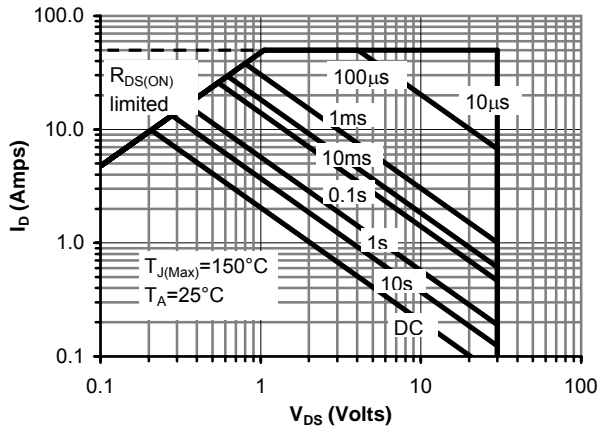


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

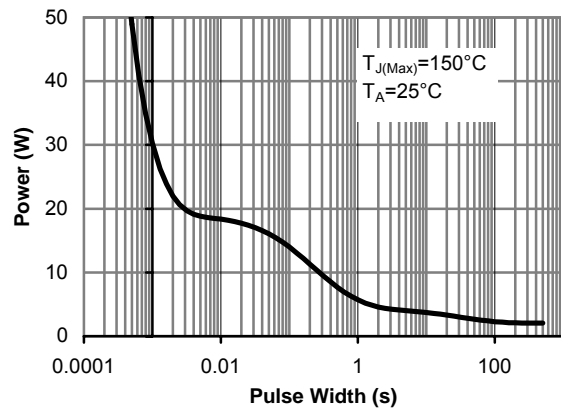


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

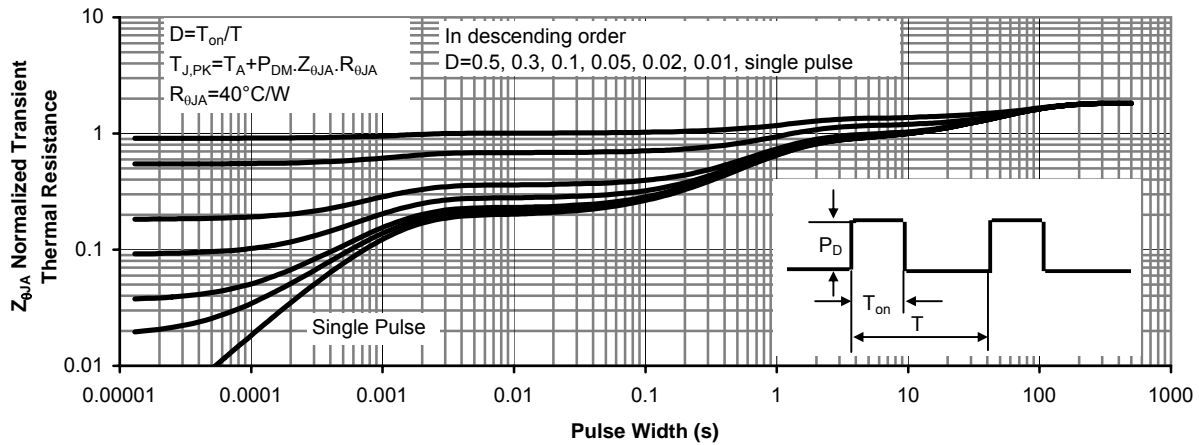


Figure 11: Normalized Maximum Transient Thermal Impedance